NCE Automotive N-Channel Super Trench Power MOSFET

Description

The NCEAP40T11G uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{DS(ON)}$ and Q_g. This device is ideal for high-frequency switching and synchronous rectification.

Application

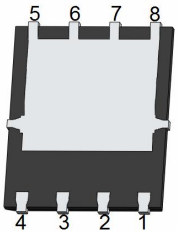
- Automotive application
- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

General Features

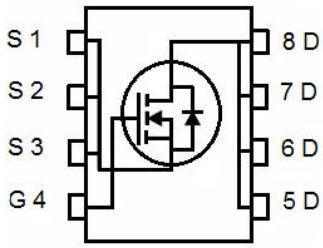
- V_{DS} =40V,I_D =150A
  $R_{DS(ON)}$=2.2mΩ (typical) @ V_{GS}=10V
  $R_{DS(ON)}$=3.3mΩ (typical) @ V_{GS}=4.5V
- Excellent gate charge x $R_{DS(on)}$ product(FOM)
- Very low on-resistance $R_{DS(on)}$
- 175 °C operating temperature
- Pb-free lead plating
- 100% UIS tested
- 100% ΔVds tested
- **AEC-Q101 qualified**

DFN 5X6

Top View



Bottom View



Schematic Diagram

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
AP40T11G	NCEAP40T11G	DFN5X6-8L	-	-	-

Absolute Maximum Ratings (T_C=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	40	V
Gate-Source Voltage	V_{GS}	±20	V
Drain Current-Continuous	I_D	150	A
Drain Current-Continuous(T_C=100℃)	I_D (100℃)	106	A
Pulsed Drain Current	I_{DM}	600	A
Maximum Power Dissipation	P_D	120	W
Derating factor	-	0.8	W/℃
Single pulse avalanche energy (Note 1)	E_{AS}	500	mJ
Operating Junction and Storage Temperature Range	T_J,T_{STG}	-55 To 175	℃

Thermal Characteristic

Thermal Resistance,Junction-to-Case	$R_{\theta JC}$	1.25	℃/W

Electrical Characteristics (T_C=25℃unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=250μA	40	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=40V,V_{GS}=0V	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	V_{GS}=±20V,V_{DS}=0V	-	-	±100	nA
On Characteristics						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=250μA	1.2	1.7	2.2	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=10V, I_D=20A	-	2.2	2.8	mΩ
		V_{GS}=4.5V, I_D=20A	-	3.3	4.0	mΩ
Forward Transconductance	g_{FS}	V_{DS}=5V,I_D=20A	-	60	-	S
Dynamic Characteristics						
Input Capacitance	C_{lss}	V_{DS}=20V,V_{GS}=0V, F=1.0MHz	-	3510	-	pF
Output Capacitance	C_{oss}		-	860	-	pF
Reverse Transfer Capacitance	C_{rss}		-	60	-	pF
Switching Characteristics (Note 2)						
Turn-on Delay Time	$t_{d(on)}$	V_{DD}=20V,I_D=20A V_{GS}=10V,R_G=1.6Ω	-	10.5	-	nS
Turn-on Rise Time	t_r		-	4	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	35	-	nS
Turn-Off Fall Time	t_f		-	5	-	nS
Total Gate Charge	Q_g	V_{DS}=20V,I_D=20A, V_{GS}=10V	-	60	-	nC
Gate-Source Charge	Q_{gs}		-	9.9	-	nC
Gate-Drain Charge	Q_{gd}		-	9.5	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage	V_{SD}	V_{GS}=0V,I_S=20A	-	-	1.2	V
Diode Forward Current	I_S		-	-	150	A
Reverse Recovery Time	t_{rr}	T_J = 25°C, I_F = I_S di/dt = 100A/μs	-	24	-	nS
Reverse Recovery Charge	Qrr		-	68	-	nC

Notes:

1.EAS condition : Tj=25℃,V_{DD}=20V,V_G=10V,L=0.5mH,Rg=25Ω
2.Guaranteed by design, not subject to production
3.These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of TJ(MAX)=175° C. The SOA curve provides a single pulse rating.

Typical Electrical and Thermal Characteristics

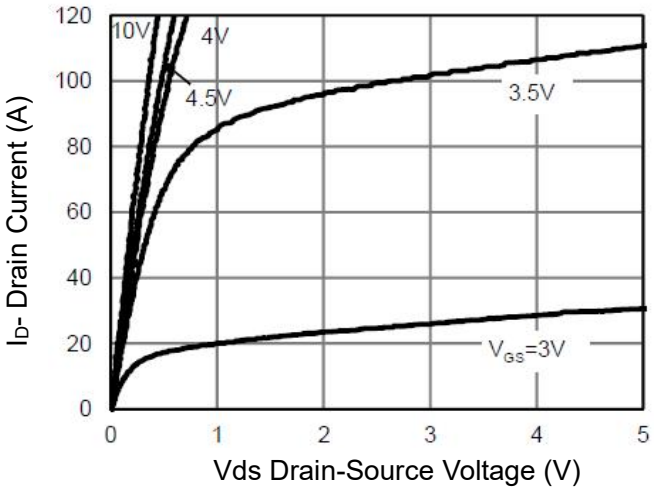


Figure 1 Output Characteristics

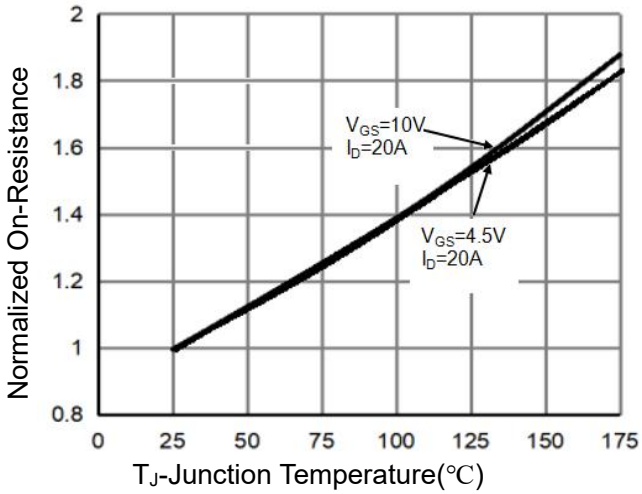


Figure 4 Rdson-JunctionTemperature

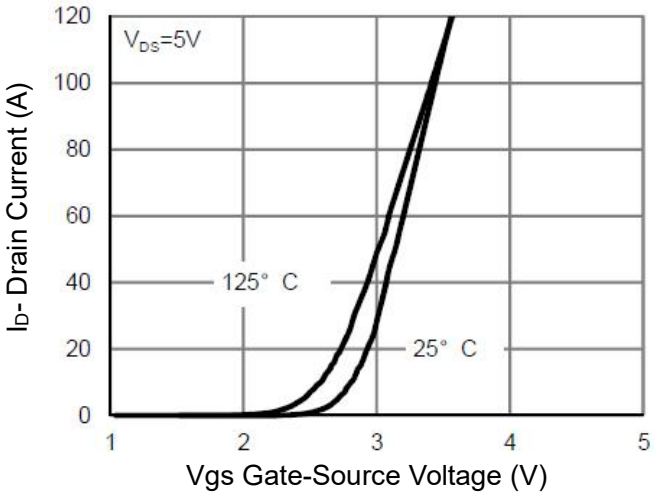


Figure 2 Transfer Characteristics

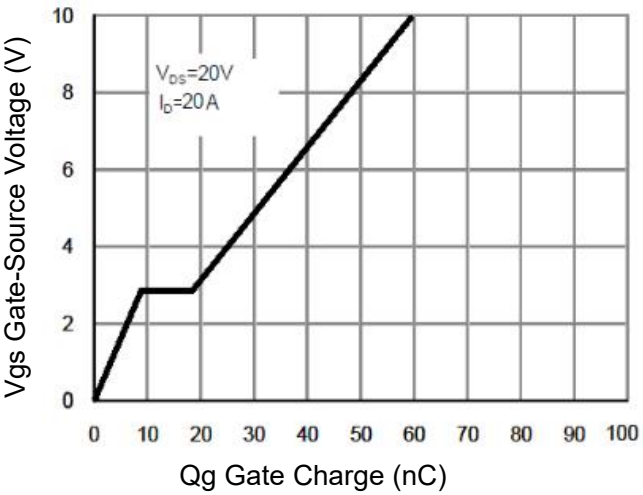


Figure 5 Gate Charge

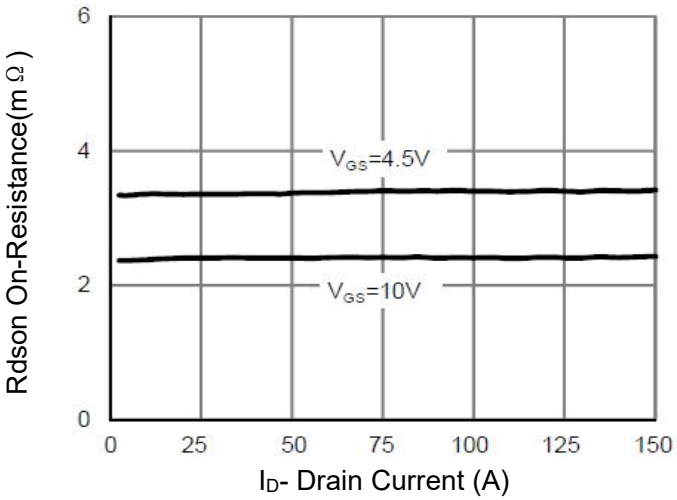


Figure 3 Rdson- Drain Current

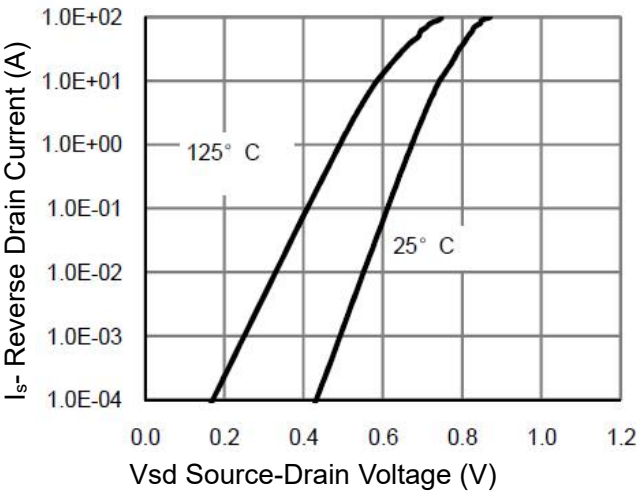


Figure 6 Source- Drain Diode Forward

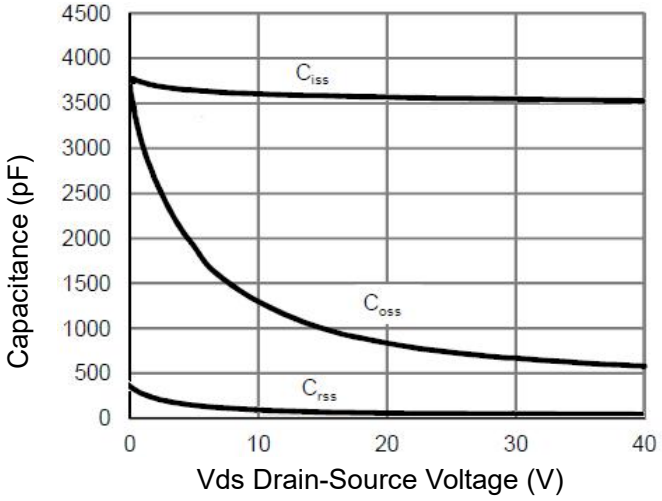


Figure 7 Capacitance vs Vds

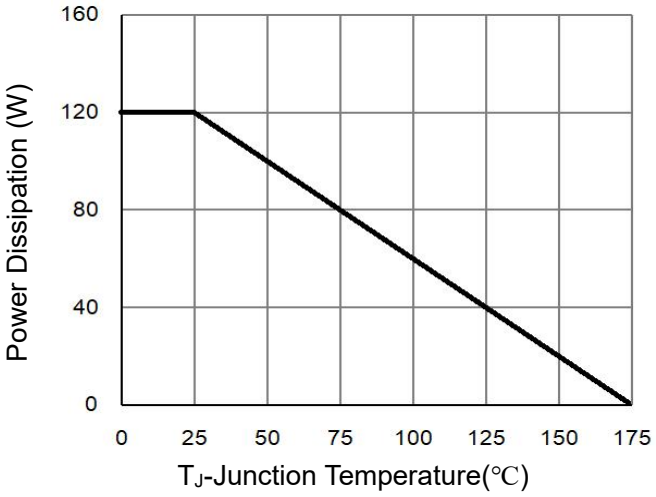


Figure 9 Power De-rating

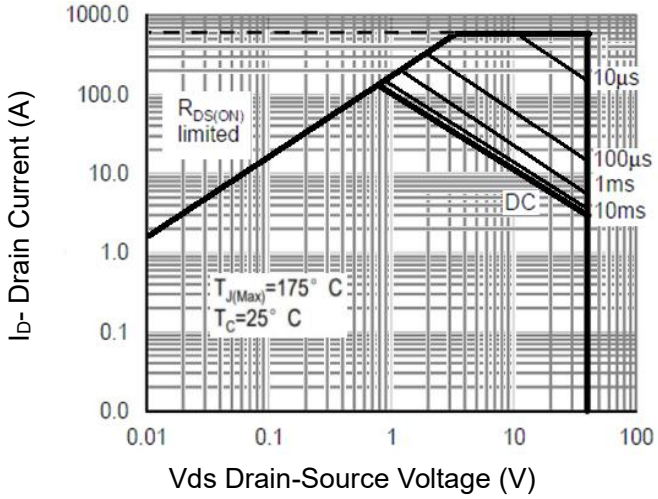


Figure 8 Safe Operation Area (Note3)

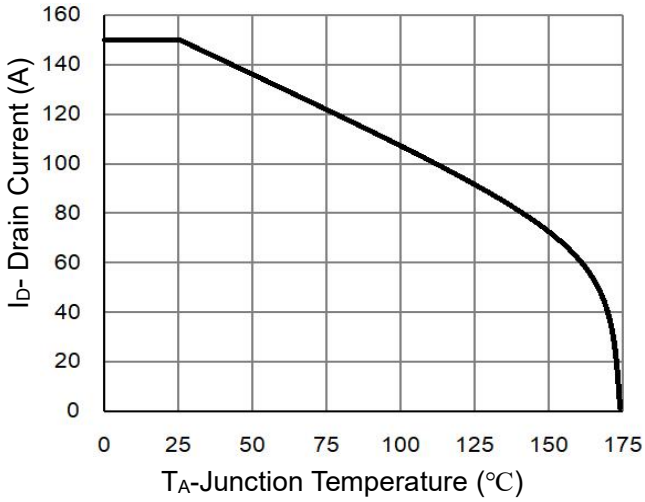


Figure 10 Current De-rating

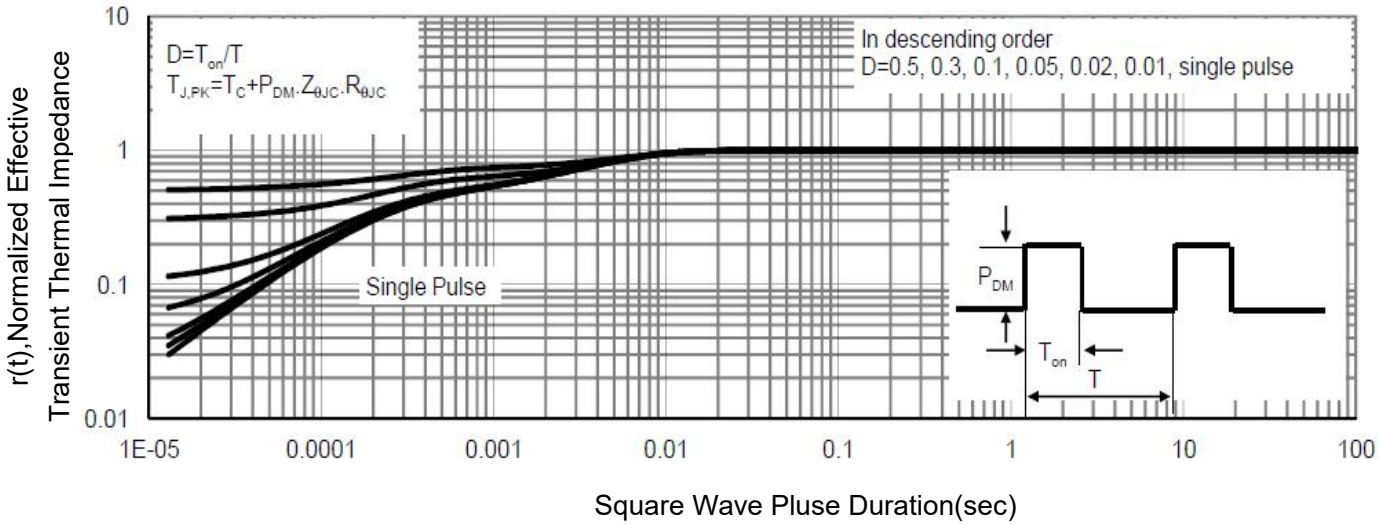
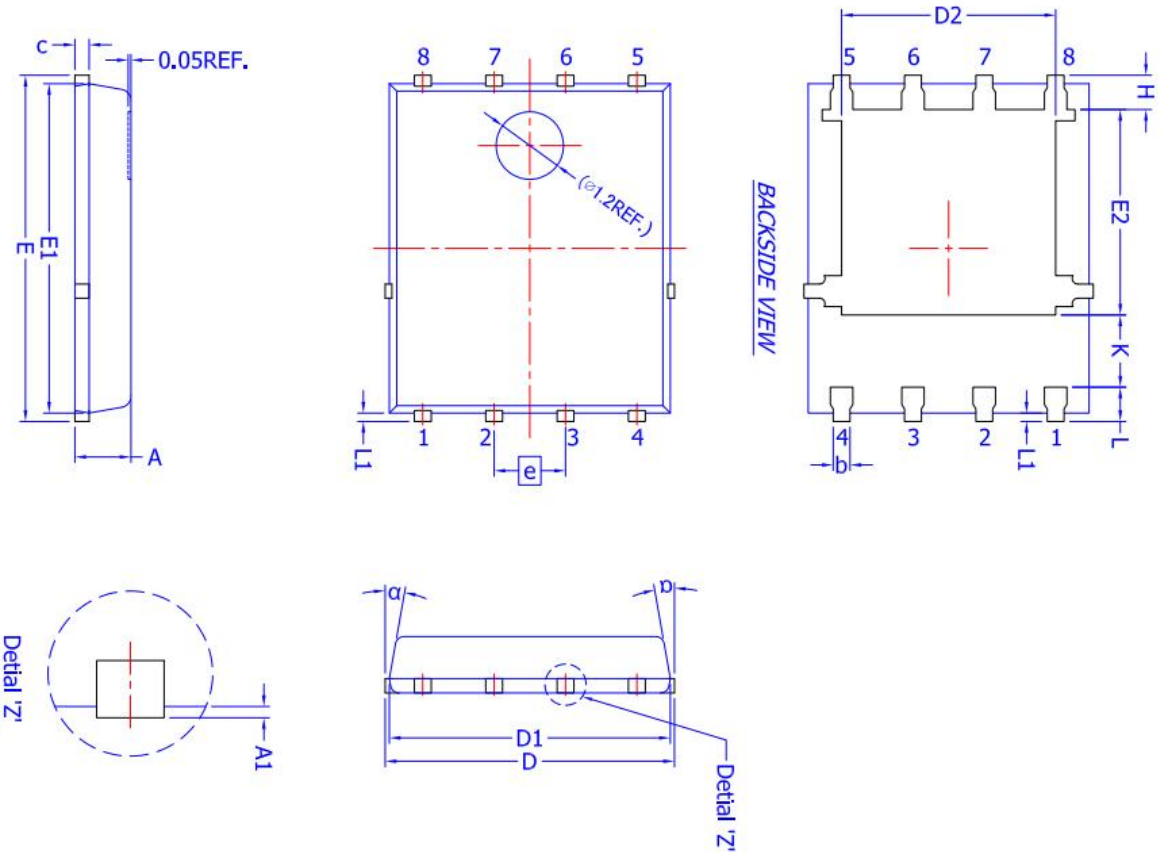


Figure 11 Normalized Maximum Transient Thermal Impedance

DFN5X6-8L Package Information



DIM.	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.90	1.00	1.10
A1	0	-	0.05
b	0.30	0.40	0.50
c	0.20	0.25	0.30
D	5.15 BSC		
D1	5.00 BSC		
D2	3.76	3.81	3.86
E	6.15 BSC		
E1	5.80	5.85	5.90
E2	3.45	3.65	3.85
e	1.27 BSC		
H	0.51	0.61	0.71
K	1.10	-	-
L	0.51	0.61	0.71
L1	0.08	0.15	0.23
α	10°	11°	12°

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